

U.S.S.N. 10/792,147

Specification Amendments

Please replace paragraph [0003] with the following rewritten paragraph:

[0003] Alignment is especially critical where ~~mere~~ a number of layers have already been deposited on the wafer. Subsequent deposition of other layers in such instances usually requires that the alignment marks on the wafer be exposed for proper overlay of the silicon dioxide or other layers. Overlay accuracy within photolithography becomes more stringent as the critical dimensions (CD's) and other dimensions of the semiconductor designs become smaller and smaller.